

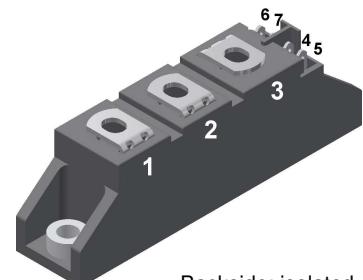
Thyristor Module

$V_{RRM} = 2 \times 1600 \text{ V}$
 $I_{TAV} = 60 \text{ A}$
 $V_T = 1.24 \text{ V}$

Phase leg

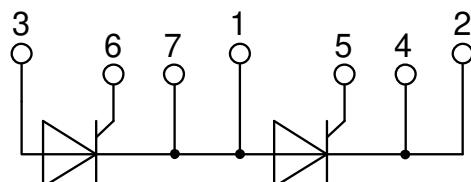
Part number

MCC56-16io1B



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

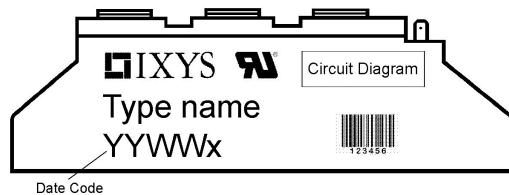
Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1600 V$ $V_{R/D} = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		200 5	μA mA
V_T	forward voltage drop	$I_T = 100 A$ $I_T = 200 A$ $I_T = 100 A$ $I_T = 200 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.26 1.57 1.24 1.62	V V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 125^\circ C$		60	A
$I_{T(RMS)}$	RMS forward current	180° sine			94	A
V_{T0} r_T	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 125^\circ C$		0.85 3.7	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.45	K/W
R_{thCH}	thermal resistance case to heatsink			0.20		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		222	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 125^\circ C$ $V_R = 0 V$		1.50 1.62 1.28 1.38	kA kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 125^\circ C$ $V_R = 0 V$		11.3 10.9 8.13 7.87	kA^2s kA^2s kA^2s kA^2s
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	74		pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$ $t_p = 300 \mu s$	$T_C = 125^\circ C$		10 5 0.5	W W W
P_{GAV}	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^\circ C; f = 50 \text{ Hz}$ repetitive, $I_T = 150 A$ $t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$ $I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 60 A$			150	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^\circ C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		1.5 1.6	V V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		100 200	mA mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10 \mu s$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		450	mA
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		2	μs
t_q	turn-off time	$V_R = 100 V; I_T = 150 A; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 100^\circ C$ $di/dt = 10 A/\mu s dv/dt = 20 V/\mu s t_p = 200 \mu s$		150		μs

Package TO-240AA			Ratings		
Symbol	Definition	Conditions	min.	typ.	max.
I_{RMS}	RMS current	per terminal			200 A
T_{VJ}	virtual junction temperature		-40		125 °C
T_{op}	operation temperature		-40		100 °C
T_{stg}	storage temperature		-40		125 °C
Weight				81	g
M_D	mounting torque		2.5		4 Nm
M_T	terminal torque		2.5		4 Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air		terminal to terminal	13.0	9.7 mm
$d_{Spb/Apb}$			terminal to backside	16.0	16.0 mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3600 V 3000 V



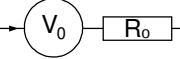
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC56-16io1B	MCC56-16io1B	Box	36	452769

Similar Part	Package	Voltage class
MCMA65P1600TA	TO-240AA-1B	1600
MCMA85P1600TA	TO-240AA-1B	1600

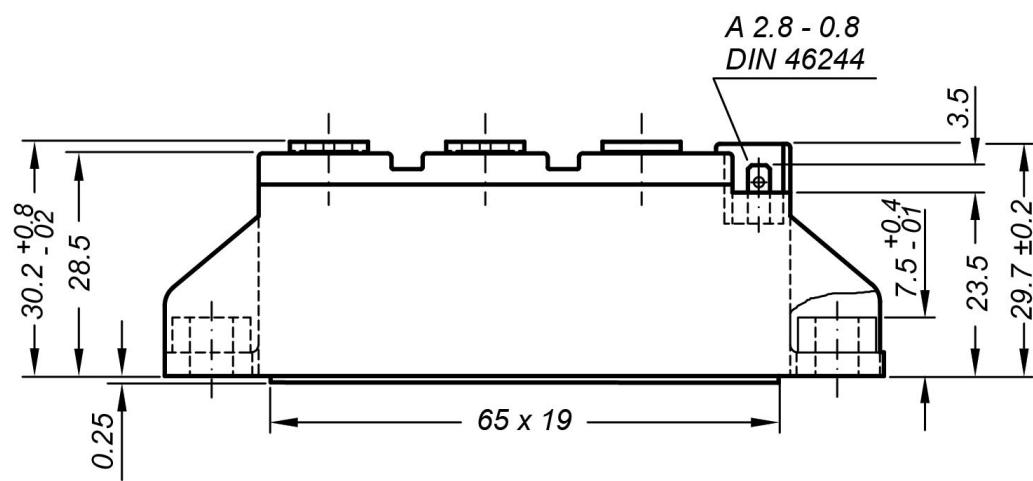
Equivalent Circuits for Simulation

* on die level

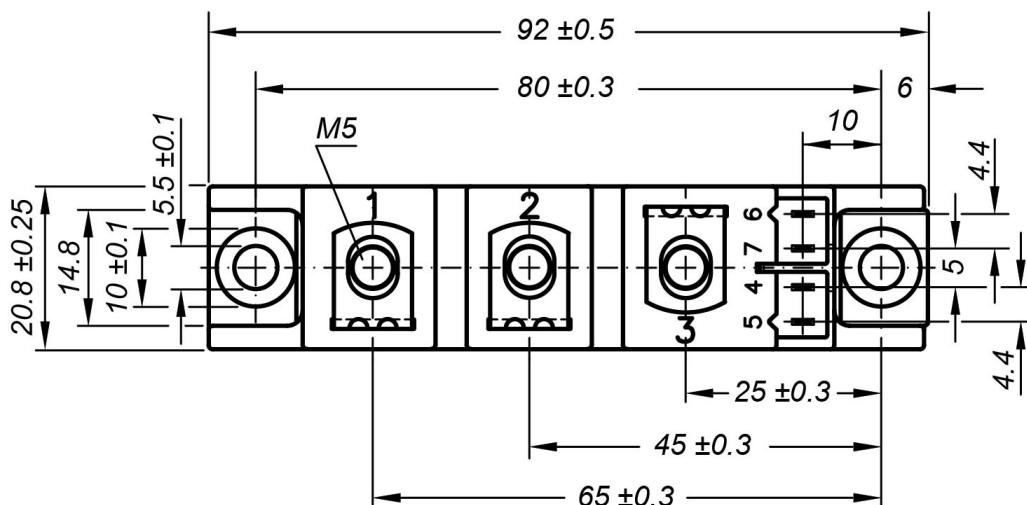
$T_{VJ} = 125$ °C

	Thyristor	
$V_{0\max}$	threshold voltage	0.85 V
$R_{0\max}$	slope resistance *	2.5 mΩ

Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



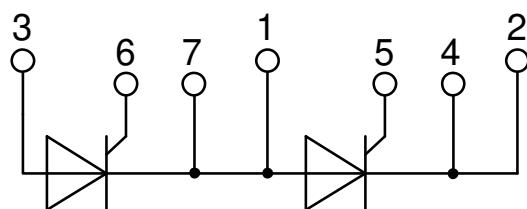
Optional accessories: Keyed gate/cathode twin plugs

Wire length: 350 mm, gate = white, cathode = red

UL 758, style 3751

Type ZY 200L (L = Left for pin pair 4/5)

Type ZY 200R (R = Right for pin pair 6/7)



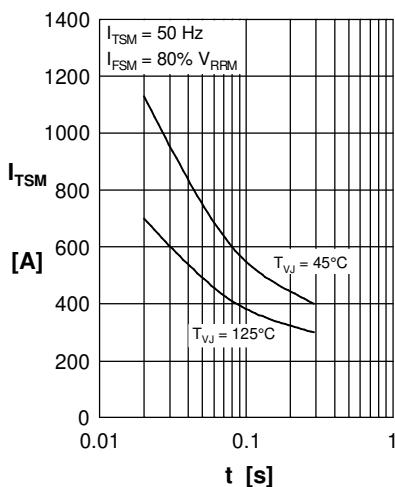
Thyristor

Fig. 1 Surge overload current I_{TSM} ,
 I_{FSM} : Crest value, t: duration

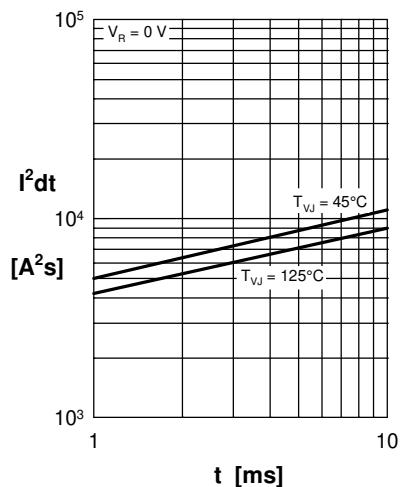


Fig. 2 $I^2 t$ versus time (1-10 ms)

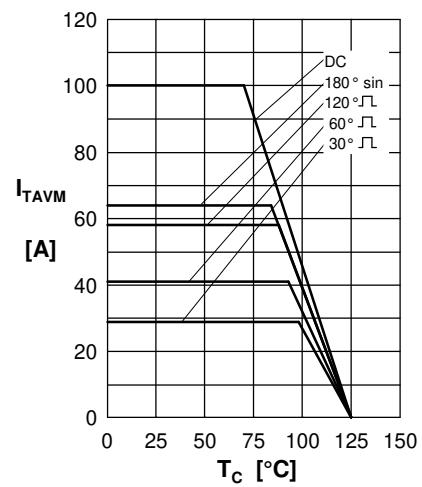


Fig. 3 Max. forward current
at case temperature

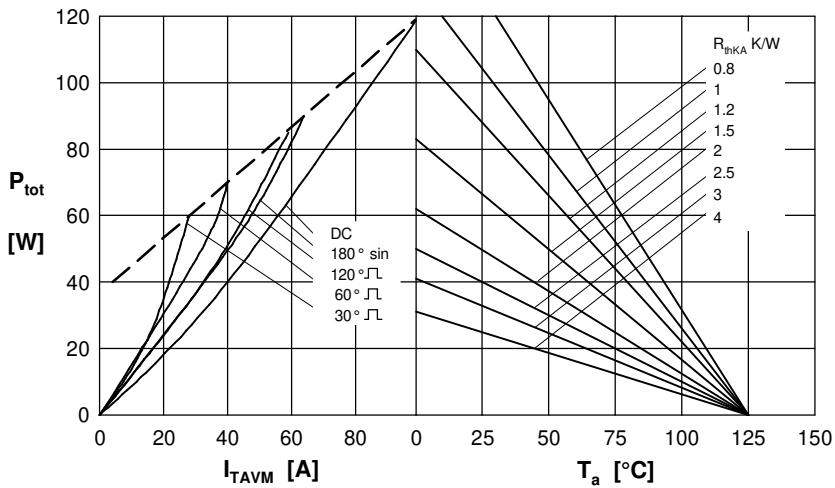


Fig. 4 Power dissipation vs. on-state current & ambient temperature
(per thyristor or diode)

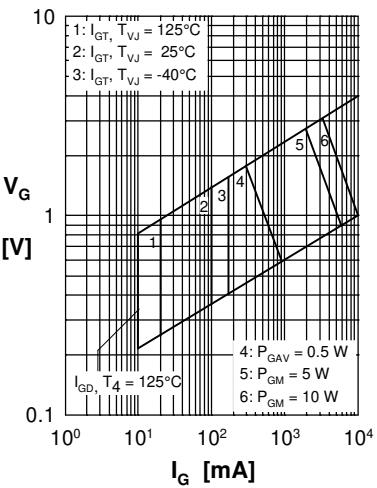


Fig. 5 Gate trigger characteristics

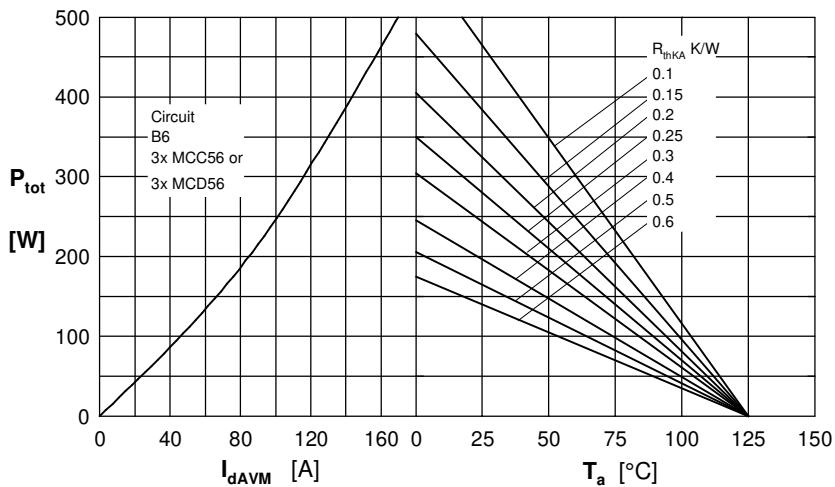


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

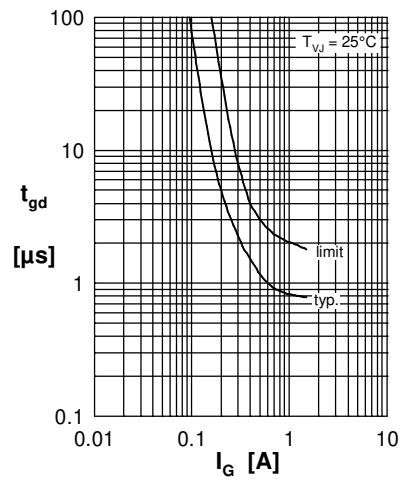


Fig. 7 Gate trigger delay time

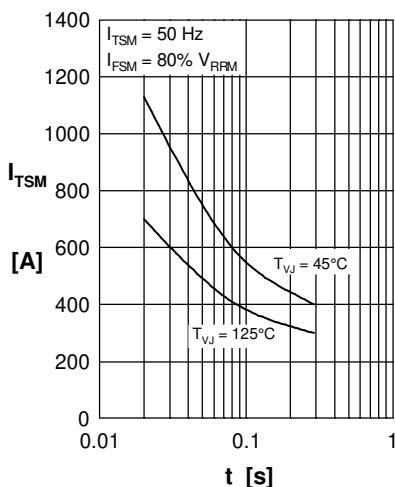
Thyristor

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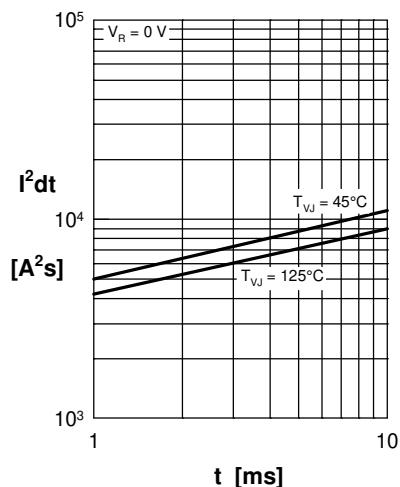


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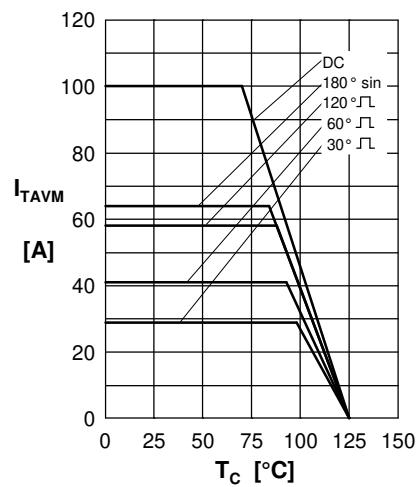


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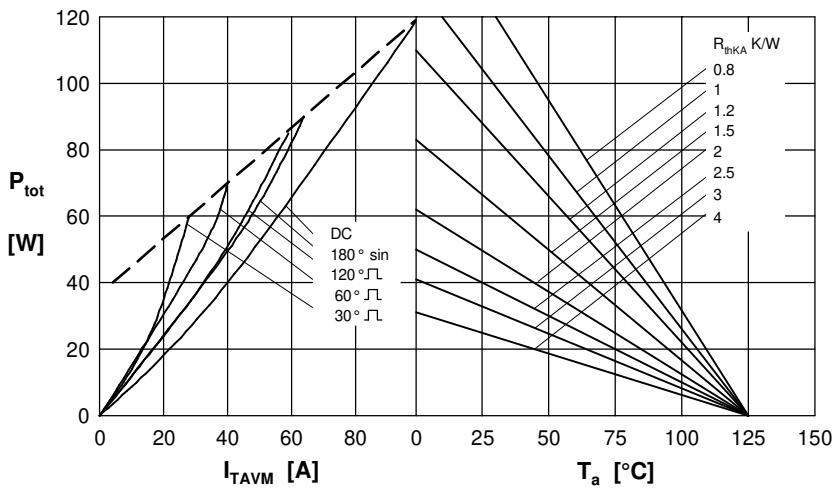


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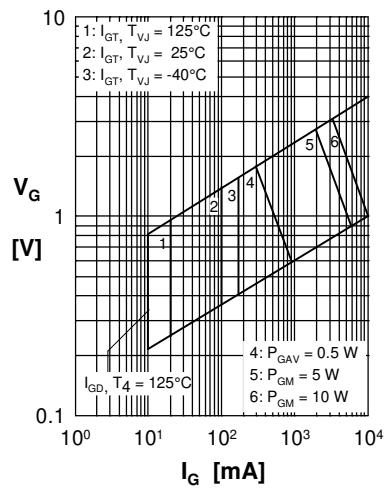


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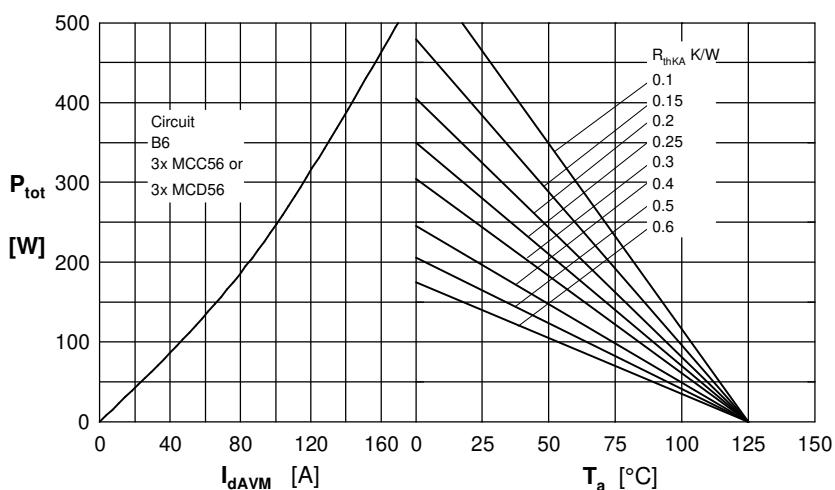


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

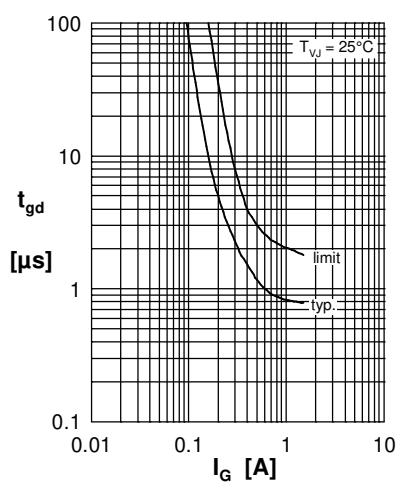


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